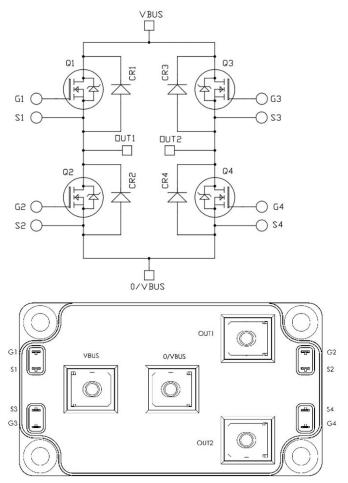
# MSCSM70HM038CAG

# **Full Bridge SiC Power Module**

## **Product Overview**

The MSCSM70HM038CAG device is a 700 V/464 A full bridge silicon carbide (SiC) power module.



All ratings at  $T_J$  = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are the key features of MSCSM70HM038CAG device:

- · SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High temperature performance
- · SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- · Kelvin source for easy drive
- · Low stray inductance
- M5 power connectors
- · Aluminum Nitride (AIN) substrate for improved thermal performance

#### **Benefits**

The following are the benefits of MSCSM70HM038CAG device:

- · High efficiency converter
- · Outstanding performance at high-frequency operation
- · Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- · RoHS Compliant

### **Applications**

The following are the applications of MSCSM70HM038CAG device:

- · Welding converters
- Switched mode power supplies
- · Uninterruptible power supplies
- EV motor and traction drive

## 1. Electrical Specifications

The following sections show the electrical specifications of the MSCSM70HM038CAG device.

## 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the MSCSM70HM038CAG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V <sub>DSS</sub>	Drain-Source voltage	Drain-Source voltage		V
I <sub>D</sub>	Continuous drain current	Continuous drain current T <sub>C</sub> = 25 °C		А
	T <sub>C</sub> = 80 °C		369	
I <sub>DM</sub>	Pulsed drain current	Pulsed drain current		
V <sub>GS</sub>	Gate-Source voltage	Gate-Source voltage		V
R <sub>DS(on)</sub>	Drain-Source ON resistance	Drain-Source ON resistance		mΩ
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	1277	W

The following table lists the electrical characteristics (per SiC MOSFET) of the MSCSM70HM038CAG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 700 V		_	_	400	μΑ
R <sub>DS(on)</sub>	Drain-Source on	V <sub>GS</sub> = 20 V	T <sub>J</sub> = 25 °C	_	3.8	4.8	mΩ
	resistance	I <sub>D</sub> = 160 A	T <sub>J</sub> = 175 °C	_	4.8	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ ; $I_D = 16 \text{ mA}$		1.9	2.4	_	V
I <sub>GSS</sub>	Gate-Source leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V		_	_	400	nA

The following table lists the dynamic characteristics (per SiC MOSFET) of the MSCSM70HM038CAG device.

**Table 1-3. Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0 V		_	18	_	nF
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 700 V		_	2	_	
C <sub>rss</sub>	Reverse transfer capacitance	f = 1 MHz		_	0.11	_	
$Q_g$	Total gate charge	V <sub>GS</sub> = -5 V/20 V		_	860	_	nC
Q <sub>gs</sub>	Gate-source charge	V <sub>Bus</sub> = 470 V		_	232	_	
$Q_{gd}$	Gate-drain charge	I <sub>D</sub> = 160 A	_	140	_		
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5 V/20 V		_	78	_	ns
T <sub>r</sub>	Rise time	V <sub>Bus</sub> = 400 V		_	125	_	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 320 A		_	214	_	
T <sub>f</sub>	Fall time	$T_J = 150 ^{\circ}\text{C}$ $R_{GON} = 7 ^{\Omega}$ $R_{GOFF} = 4 ^{\Omega}$			92	_	
E <sub>on</sub>	Turn-on energy	V <sub>GS</sub> = -5 V/20 V	T <sub>J</sub> = 150 °C	_	4.1	_	mJ
E <sub>off</sub>	Turn-off energy	$V_{Bus} = 400 \text{ V}$ $I_D = 320 \text{ A}$ $R_{GON} = 7 \Omega$ $R_{GOFF} = 4 \Omega$	T <sub>J</sub> = 150 °C	_	7		mJ
R <sub>Gint</sub>	Internal gate resistance			_	1.4	_	Ω
R <sub>thJC</sub>	Junction-to-case thermal resistance			_	_	0.117	°C/W

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the MSCSM70HM038CAG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
$V_{SD}$	Diode forward voltage	V <sub>GS</sub> = 0 V; I <sub>SD</sub> = 160 A	_	3.4	_	V
		$V_{GS} = -5 \text{ V}; I_{SD} = 160 \text{ A}$	_	3.8	_	
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 160 A	_	40	_	ns
Q <sub>rr</sub>	Reverse recovery charge	$V_{GS} = -5 V$	_	2	_	μC
I <sub>rr</sub>	Reverse recovery current	$V_R = 400 \text{ V}$ $di_F/dt = 4000 \text{ A/}\mu\text{s}$	_	76	_	A

## 1.2 SiC Schottky Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC Schottky diode ratings and characteristics of the MSCSM70HM038CAG device.

Table 1-5. SiC Schottky Diode Ratings and Characteristics (Per SiC Diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak repetitive reverse voltage	_		_	_	700	V
I <sub>RRM</sub>	Reverse leakage current	V <sub>R</sub> = 700 V	T <sub>J</sub> = 25 °C	_	60	800	μA
			T <sub>J</sub> = 175 °C	_	1000	_	
I <sub>F</sub>	DC forward current	_	T <sub>C</sub> = 65 °C	_	200	_	Α
V <sub>F</sub>	Diode forward voltage	age I <sub>F</sub> = 200 A T <sub>J</sub> =	T <sub>J</sub> = 25 °C	_	1.5	1.8	V
			T <sub>J</sub> = 175 °C	_	1.9	_	
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 400 V		_	532	_	nC
С	Total capacitance	ce $f = 1 \text{ MHz}, V_R = 200 \text{ V}$ $f = 1 \text{ MHz}, V_R = 400 \text{ V}$		_	992	_	pF
				_	864	_	
R <sub>thJC</sub>	Junction-to-case thermal re	sistance		_	_	0.246	°C/W

## 1.3 Thermal and Package Characteristics

The following table lists the package characteristics of the MSCSM70HM038CAG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to ca	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz				
t <sub>J</sub>	Operating junction temperature range			-40	175	°C
T <sub>JOP</sub>	Recommended junction temperature und	er switching co	onditions	-40	T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage case temperature	-40	125			
T <sub>C</sub>	Operating case temperature	Operating case temperature				
Torque	Mounting torque	To heatsink	M6	3	5	N.m
	For terminals				3.5	
Wt	Package weight	_	300	g		

### 1.4 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM70HM038CAG device.

Figure 1-1. Maximum Thermal Impedance

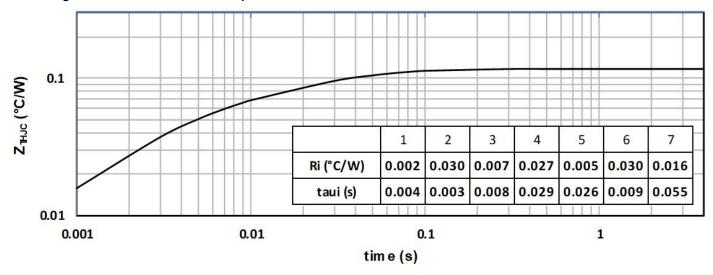


Figure 1-2. Output Characteristics,  $T_J = 25$  °C

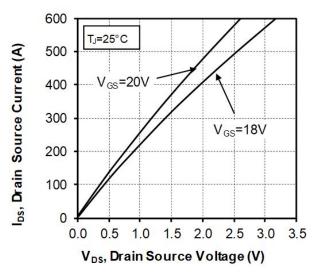
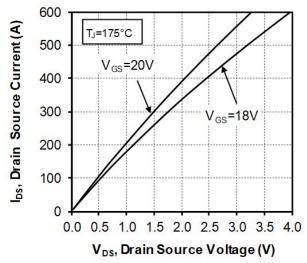


Figure 1-3. Output Characteristics, T<sub>J</sub> = 175 °C



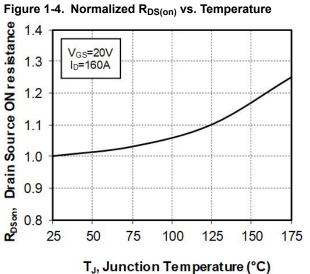


Figure 1-5. Transfer Characteristics 600 I<sub>DS</sub>, Drain Source Current (A) 500 400 TJ=175°C 300 200 100 T<sub>J</sub>=25°C 0 6 8 4 10 12 V<sub>GS</sub>, Gate Source Voltage (V)

Figure 1-6. Capacitance vs. Drain Source Voltage

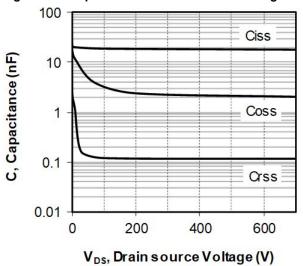
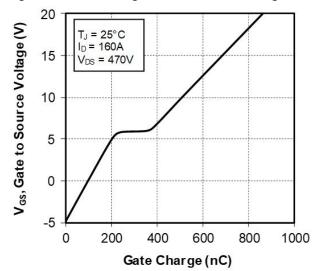


Figure 1-7. Gate Charge vs. Gate Source Voltage



## MSCSM70HM038CAG

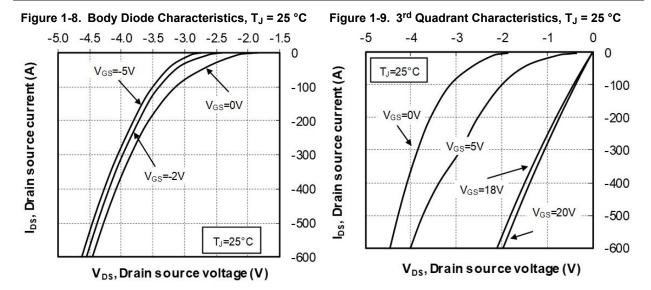


Figure 1-10. Body Diode Characteristics,  $T_J$  = 175 °C Figure 1-11.  $3^{rd}$  Quadrant Characteristics,  $T_J$  = 175 °C

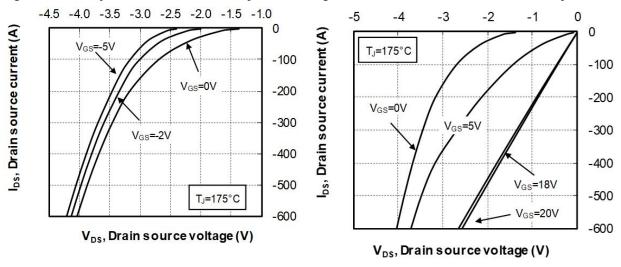


Figure 1-12. Switching Energy vs. Current

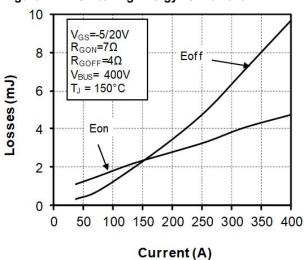


Figure 1-13. Turn On Energy vs. Rg

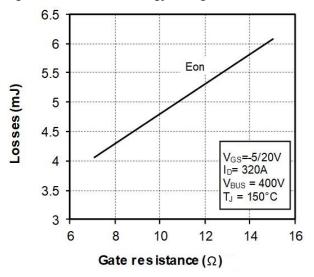


Figure 1-14. Turn Off Energy vs. Rg

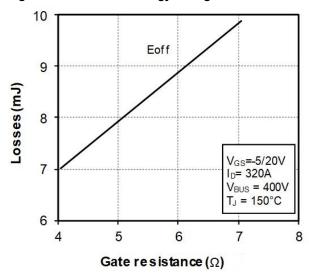
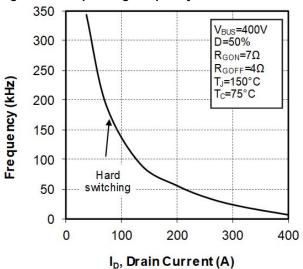


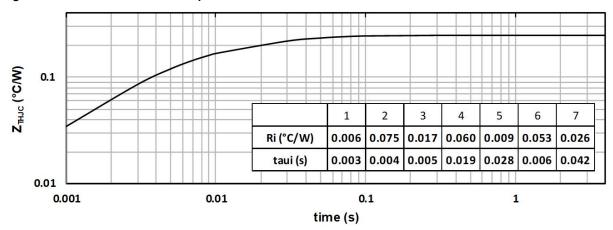
Figure 1-15. Operating Frequency vs. Drain Current



### 1.5 Typical SiC Diode Performance Curve

The following figures show the SiC diode performance curves of the MSCSM70HM038CAG device.

Figure 1-16. Maximum Thermal Impedance



C, Capacitance (nF)

Figure 1-17. Forward Characteristics

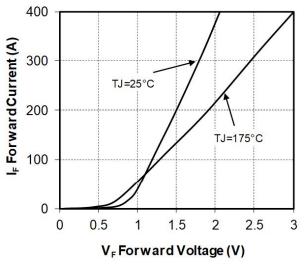
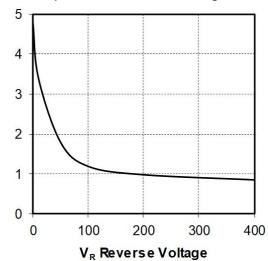


Figure 1-18. Capacitance vs. Reverse Voltage



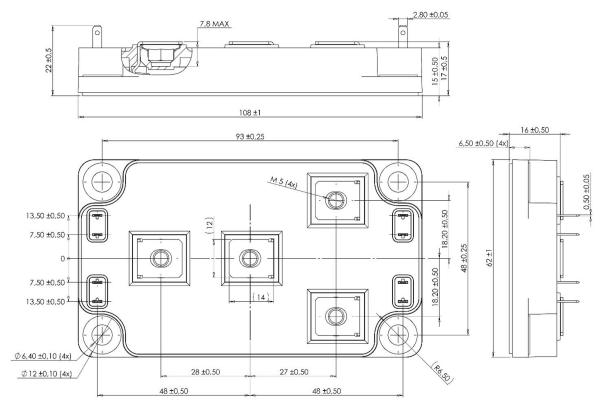
## 2. Package Specifications

The following section shows the package specification of the MSCSM70HM038CAG device.

## 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70HM038CAG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See application note APT0601—Mounting Instructions for SP6 Power Modules.

# 3. Revision History

Revision	Date	Description
Α	04/2021	This is the first publication of this document.

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